

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicants: Toshiharu Furukawa, et al. Confirmation No.: 6082  
Art Unit: 2818  
Serial No.: 10/814,482  
Examiner: David J. Goodwin  
Filed: March 31, 2004  
Atty. Docket No.: ROC9200300399US1  
For: METHOD FOR FABRICATING STRAINED SILICON-ON-  
INSULATOR STRUCTURES AND STRAINED SILICON-ON-  
INSULATOR STRUCTURES FORMED THEREBY

**AMENDMENT UNDER 37 C.F.R. § 1.111**

Mail Stop AMENDMENT  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In reply to the non-final Office Action dated May 11, 2006, please amend the above-identified application as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Amendments to the Claims** are reflected in the listing of claims that begins on page 3 of this paper.

**Amendments to the Drawings** begin on page 6 of this paper and include both an attached replacement sheet and an annotated sheet showing changes.

**Remarks** begin on page 7 of this paper.

An **Appendix** including amended drawing figures is attached following page 9 of this paper.